

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Atty. Docket

PONOMAREV

NL 031497

Serial No.

Group Art Unit

Filed: CONCURRENTLY

Ex.

METHOD OF FORMING A STRAINED SI-CHANNEL IN A MOSFET STRUCTURE

Commissioner for Patents  
Alexandria, VA 22313-1450

PRELIMINARY AMENDMENT

Sir:

Prior to calculation of the filing fee and examination, please  
amend the above-identified application as follows: